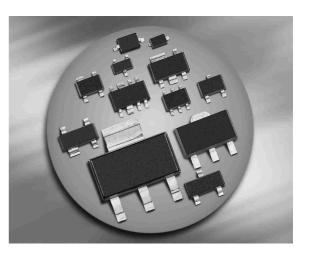


BBY56...

### Silicon Tuning Diode

- Excellent linearity
- Low series resistance
- Designed for low tuning voltage operation for VCO's in mobile communications equipment
- Very low capacitance spread
- Pb-free (RoHS compliant) package





BBY56-02V BBY56-02W BBY56-03W



Туре	Package	Configuration	Marking		
BBY56-02V	SC79	single	9		
BBY56-02W*	SCD80	single	66		
BBY56-03W	SOD323	single	red 6		

\* Not for new design

### **Maximum Ratings** at $T_A$ = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V <sub>R</sub>	10	V
Forward current	I <sub>F</sub>	20	mA
Operating temperature range	T <sub>op</sub>	-55150	°C
Storage temperature	T <sub>Stg</sub>	-55150	



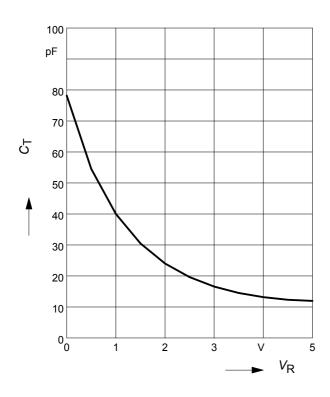
Parameter	Symbol		Unit		
		min.	typ.	max.	
DC Characteristics					
Reverse current	I <sub>R</sub>				nA
<i>V</i> <sub>R</sub> = 6 V		-	-	5	
$V_{\rm R}$ = 6 V, $T_{\rm A}$ = 85 °C		-	-	100	
AC Characteristics					•
Diode capacitance	CT				pF
V <sub>R</sub> = 1 V, <i>f</i> = 1 MHz		37	40	43	
V <sub>R</sub> = 2 V, <i>f</i> = 1 MHz		22	-	25	
V <sub>R</sub> = 3 V, <i>f</i> = 1 MHz		14.8	15.8	16.8	
$V_{\rm R}$ = 4 V, <i>f</i> = 1 MHz		-	12.1	-	
Capacitance ratio	C <sub>T1</sub> /C <sub>T3</sub>				
<i>V</i> <sub>R</sub> = 1 V, <i>V</i> <sub>R</sub> = 3 V, <i>f</i> = 1 MHz		2.15	2.53	-	
$V_{\rm R}$ = 1 V, $V_{\rm R}$ = 4 V, $f$ = 1 MHz		-	3.3	-	
Series resistance	r <sub>S</sub>	-	0.25	-	Ω
V <sub>R</sub> = 1 V, <i>f</i> = 470 MHz					

#### **Electrical Characteristics** at $T_A$ = 25 °C, unless otherwise specified



**Diode capacitance**  $C_{T} = f(V_{R})$ 

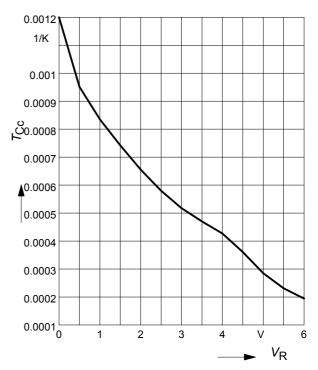
f = 1 MHz



### Temperature coefficient of the diode

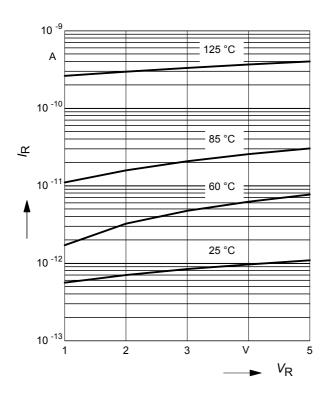
capacitance  $T_{Cc} = f(V_R)$ 

f = 1 MHz

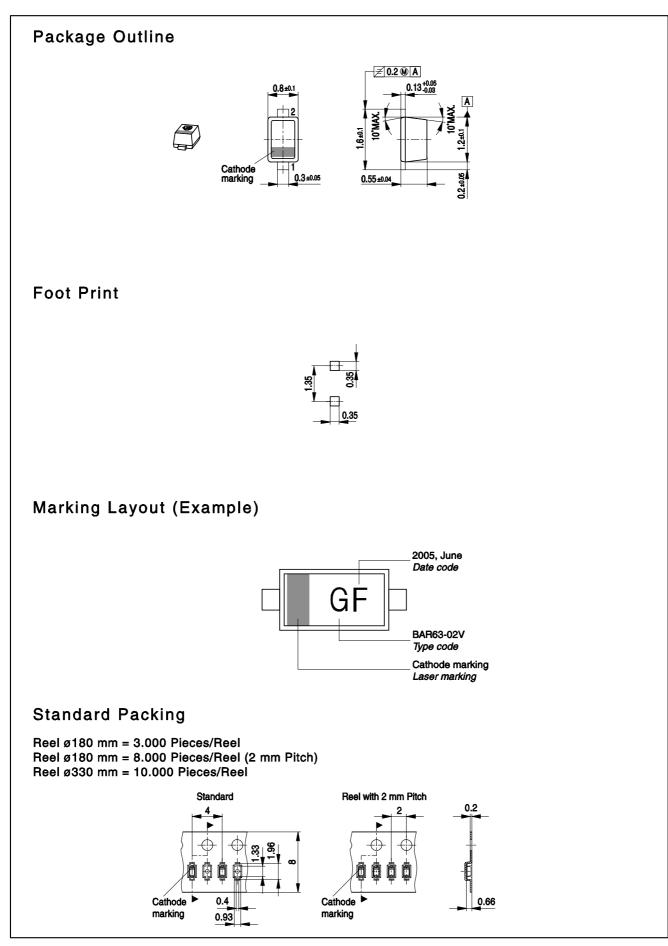


## **Reverse current** $I_{R} = f(V_{R})$

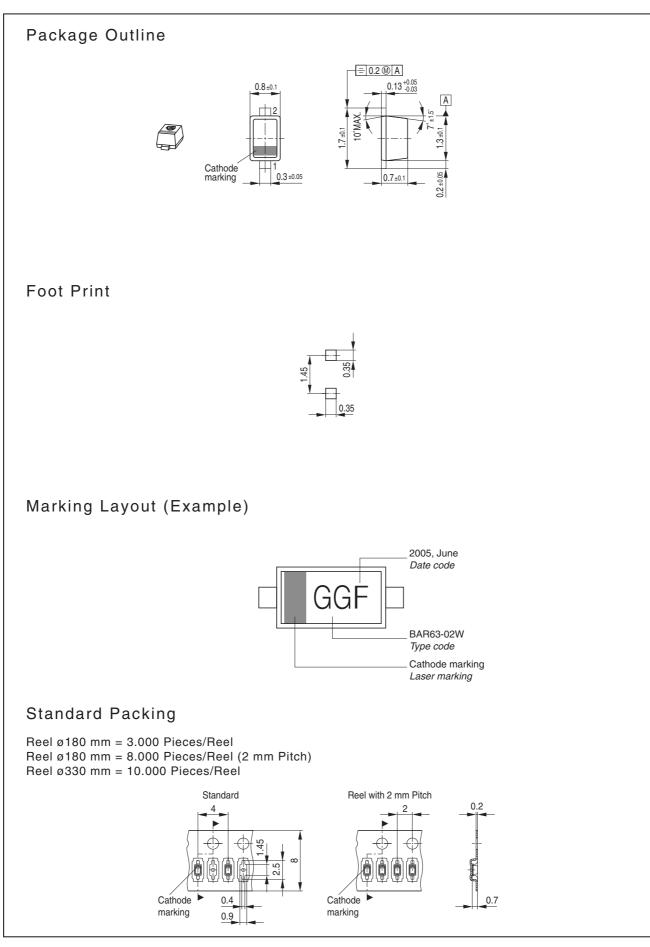
 $T_A$  = Parameter











5



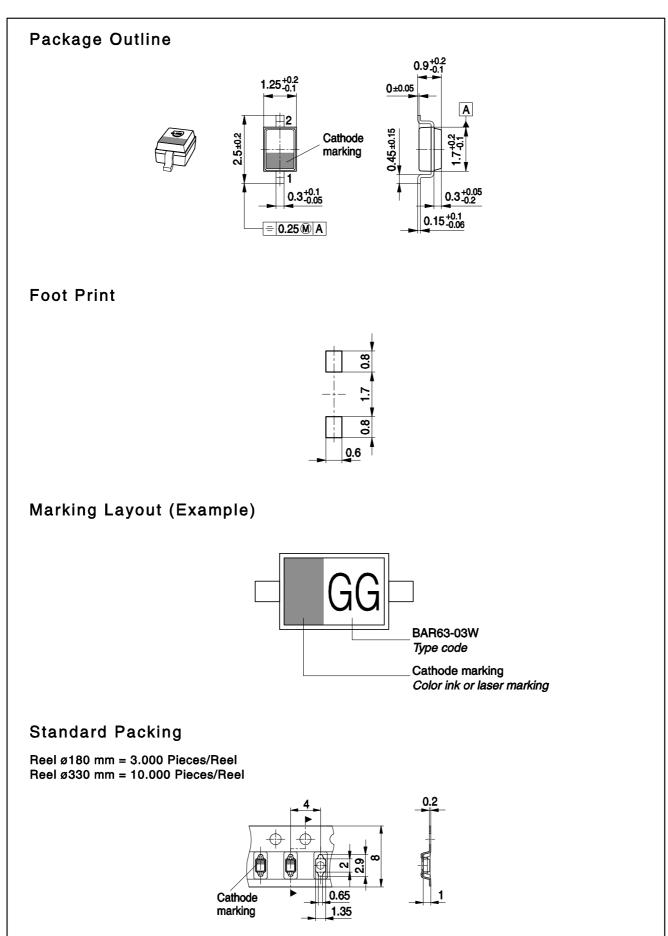
# Date Code marking for discrete packages with one digit (SCD80, SC79, SC75<sup>1)</sup>) CES-Code

Month	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014
01	а	р	А	Р	а	р	А	Р	а	р	А	Р
02	b	q	В	Q	b	q	В	Q	b	q	В	Q
03	С	r	С	R	С	r	С	R	С	r	С	R
04	d	S	D	S	d	S	D	S	d	S	D	S
05	е	t	E	Т	е	t	E	Т	е	t	Е	Т
06	f	u	F	U	f	u	F	U	f	u	F	U
07	g	V	G	V	g	V	G	V	g	V	G	V
08	h	х	Н	Х	h	х	Н	Х	h	х	Н	Х
09	j	у	J	Y	j	у	J	Y	j	у	J	Y
10	k	Z	K	Z	k	Z	K	Z	k	Z	K	Z
11	I	2	L	4	I	2	L	4	I	2	L	4
12	n	3	Ν	5	n	3	Ν	5	n	3	Ν	5

1) New Marking Layout for SC75, implemented at October 2005.

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